

General

 Vectron® Oscillators		Rev	Cage Code
		H	00136

This specification defines the design, assembly, and functional evaluation of high reliability, Space qualified, hybrid VCXOs produced by Microchip. Devices delivered to this specification represent the standardized Parts, Materials and Processes (PMP) Program developed, implemented, and certified for advanced applications and extended environments.

For more information see [Space Oscillators](#).

For technical support regarding this Hi-Rel Standard, please contact VOP-Support@microchip.com.

Applications Overview

The designs represented by these products were primarily developed for the MIL-Aerospace community. The lesser Design Pedigrees and Screening Options imbedded within DOC206218 bridge the gap between Space and COTS hardware by providing custom hardware with measures of mechanical, assembly and reliability assurance needed for Military or Ruggedized COTS environments.

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1. Applicable Documents

1.1. Specifications and Standards

The following specifications and standards form a part of this document to the extent specified herein. The issue currently in effect on the date of quotation will be the product baseline, unless otherwise specified. In the event of conflict between the texts of any references cited herein, the text of this document shall take precedence.

Table 1-1. Military

Document	Title
MIL-PRF-55310	Oscillators, Crystal Controlled, General Specification For
MIL-PRF-38534	Hybrid Microcircuits, General Specification For

Table 1-2. Standards

Document	Title
MIL-STD-202	Test Method Standard, Electronic and Electrical Component Parts
MIL-STD-883	Test Methods and Procedures for Microelectronics

Table 1-3. Other

Document	Title
DOC206251	Test Specification, DOC206218 Hybrids, Hi-Rel Standard
QSP-90100	Quality Systems Manual, Microchip
DOC011627	Identification Common Documents, Materials and Processes, Hi-Rel XO
DOC203982	DPA Specification
QSP-91502	Procedure for Electrostatic Discharge Precautions
DOC208191	Enhanced Element Evaluation for Space Level Hybrid Oscillators
DOC220429	Packaging Standards, Hi-Rel Series

2. General Requirements

2.1. Classification

All devices delivered to this specification are of hybrid technology conforming to Type 2, Class 2 of MIL-PRF-55310. Primarily developed as a Class S equivalent specification, options are imbedded within it to also produce Class B, Engineering Model and Ruggedized COTS devices. Devices carry a Class 2 ESDS classification per MIL-PRF-38534.

2.2. Item Identification

See [Ordering Part Number](#) for part number configuration.

2.3. Absolute Maximum Ratings

Table 2-1. Absolute Maximum Ratings

Parameter	Value
Supply Voltage Range (V_{CC})	-0.5 Vdc to +7.0 Vdc
Storage Temperature Range (T_{STG})	-65 °C to +125 °C
Junction Temperature (T_J)	+175 °C
Lead Temperature (soldering, 10 seconds)	+300 °C
Output Source/Sink Current	±70 mA

2.4. Design, Parts, Materials and Processes, Assembly, Inspection and Test

2.4.1. Design

The ruggedized designs implemented for these devices are proven in military and space applications under extreme environments. The design utilizes a 4-point crystal mount in compliment with Established Reliability (MIL-ER) componentry. When specified, radiation tolerant active devices up to 100 krad(Si) (RHA level R) can be included without altering the device's internal topography.

2.4.1.1. Design and Configuration Stability

Barring changes to improve performance by reselecting passive chip component values to offset component tolerances, there will not be fundamental changes to the design or assembly or parts, materials, and processes after first product delivery of that item without notification.

2.4.1.2. Environmental Integrity

Designs have passed the environmental qualification levels of MIL- PRF-55310.

2.4.2. Prohibited Parts, Materials and Processes

The items listed are prohibited for use in high reliability devices produced to this specification.

- Gold metallization of package elements without a barrier metal.
- Zinc chromate as a finish.
- Cadmium, zinc, or pure tin external or internal to the device.
- Plastic encapsulated semiconductor devices.
- Ultrasonically cleaned electronic parts.
- Heterojunction Bipolar Transistor (HBT) technology.
- 'Getter' materials

2.4.3. Assembly

Manufacturing utilizes standardized procedures, processes, and verification methods to produce MIL-PRF-55310 Class S/MIL-PRF-38534 Class K equivalent devices. MIL-PRF-38534 Group B Option 1 in-line inspection is included on radiation hardened part numbers to further verify lot pedigree. Devices are handled in accordance with Microchip document QSP-91502 (Procedure for Electrostatic Discharge Precautions). Element replacement will be as specified in MIL-PRF-38534, Rev L.

2.4.4. Inspection

The inspection requirements of MIL-PRF-55310 apply to all devices delivered to this document. Inspection conditions and standards are documented in accordance with the Quality Assurance, ISO-9001 and AS9100 derived, System of QSP-90100.

2.4.5. Test

The Screening test matrix in [Table 6-4](#) is tailored for selectable-combination testing to eliminate costs associated with the development/maintenance of device-specific documentation packages while maintaining performance integrity.

2.4.6. Marking

Device marking shall be in accordance with the requirements of MIL-PRF-55310. In addition, when devices are identified with laser marking, the Resistance to Solvents test specified in MIL-PRF-55310 Group C, MIL-PRF-55310 Qualification or MIL-PRF-38534 Group B Inspection will not be performed.

2.4.7. Ruggedized COTS Design Implementation

Design Pedigree “D” devices (see [6.2. Electrical Characteristics and Test Parameters](#)) use the same robust designs found in the other device pedigrees. They do not include the provisions of traceability or the Class-qualified componentry noted in [2.4.3. Assembly](#) and [3.1. Components](#).

3. Detail Requirements

3.1. Components

3.1.1. Crystals

Cultured quartz crystal resonators are used to provide the selected frequency for the devices. The optional use of Premium Q swept quartz can, because of its processing to remove impurities, be specified to minimize frequency drift when operating in radiation environments. In accordance with MIL-PRF-55310, the manufacturer has a documented crystal element evaluation program.

3.1.2. Passive Components

3.1.2.1. Design Pedigree E

Where available, resistors shall be Established Reliability, Failure Rate R (as a minimum) and capacitors shall be Failure Rate S. Where resistors and capacitors are not available as ER parts, and for all other passive components, the parts shall be from homogeneous manufacturing lots that have successfully completed the Enhanced Element Evaluation of DOC208191 which meets the requirements of MIL-PRF-38534 Revision L for Class K.

3.1.2.2. Design Pedigrees R, V and X

Where available, resistors shall be Established Reliability, Failure Rate R (as a minimum) and capacitors shall be Failure Rate S. Where resistors and capacitors are not available as ER parts, and for all other passive components, the parts shall be from homogeneous manufacturing lots that have successfully completed the Class K Element Evaluation of MIL-PRF-38534 Revision K for Class K.

3.1.2.3. Design Pedigrees B and C

All passive elements shall comply with the Element Evaluation requirements of MIL-PRF-55310 Class B as a minimum.

3.1.2.4. Design Pedigree D

Passive elements will be COTS level or higher.

3.1.2.5. Inductors

When used, inductors will be open construction and may use up to 47-gauge wire.

3.1.3. Microcircuits

3.1.3.1. Design Pedigree E

Microcircuits shall be from homogeneous wafer lots that meet the Enhanced Element Evaluation requirements in DOC208191 and meet the requirements of MIL-PRF-38534 Revision L for Class K.

3.1.3.2. Design Pedigree R, V and X

Microcircuits shall be from homogeneous wafer lots that have successfully completed the MIL-PRF-38534, Revision K Lot Acceptance Tests for Class K.

3.1.3.3. Design Pedigrees B and C

Microcircuits are procured from wafer lots that have successfully completed the MIL-PRF-55310 Lot Acceptance Tests for Class B as a minimum.

3.1.3.4. Design Pedigree D

Microcircuits can be COTS level or higher.

3.1.4. Semiconductors (Varactor Diode)

3.1.4.1. Design Pedigree E

Semiconductors shall be from homogeneous wafer lots that meet the Enhanced Element Evaluation requirements in DOC208191.

3.1.4.2. Design Pedigree R, V and X

Semiconductors shall be from homogeneous wafer lots that have successfully completed the MIL-PRF-38534, Revision K Lot Acceptance Tests for Class K devices as a minimum.

3.1.4.3. Design Pedigree B and C

Semiconductors are procured from wafer lots that have successfully completed the MIL-PRF-55310 Lot Acceptance Tests for Class B devices as a minimum.

3.1.4.4. Design Pedigree D

Semiconductors can be COTS level or higher.

3.1.5. Radiation

Microcircuits for Design Pedigrees E, R and V are certified to 100 krad(Si) total ionizing dose (TID), RHA level R (2X minimum margin). NSC, as the original 54ACT designer, rates the SEU LET up to 40 MeV-cm²/mg and SEL LET up to 120 MeV-cm²/mg for the FACT™ family (AN-932). Microchip conducted additional SEE testing in 2008 to verify this performance since our lot wafer testing does not include these parameters and determinations. Varactor diodes are considered radiation tolerant by design.

3.1.6. Packages

Packages are procured that meet the construction, lead materials and finishes as specified in MIL-PRF-55310. All leads are Kovar with gold plating over a nickel underplate. Package lots are evaluated in accordance with the requirements of MIL-PRF-38534. Microchip will not perform Salt Spray testing as part of MIL-PRF-55310 Group C/Qualification. In accordance with MIL-PRF-55310, package evaluation results for salt atmosphere will be substituted for Salt Spray testing during MIL-PRF-55310 Group C/Qualification. In addition, we perform Terminal Strength testing per MILSTD-202, Method 211, Test Condition C with the following exceptions: Load shall be 3 oz ± 0.3 oz, three bends at 90°.

3.1.7. Traceability and Homogeneity

All design pedigrees except option D have active device lots that are traceable to the manufacturer's individual wafer; all other elements and materials are traceable to their manufacturer and incoming inspection lots. Design pedigrees E, R, V and X have homogeneous material. In addition, swept quartz crystals are traceable to the quartz bar and the processing details of the autoclave lot. A production lot, as defined by Microchip, is all oscillators that have been kitted and built as a single group. The maximum deliverable quantity with a single lot date code is 225 units. Order quantities that exceed 225 units will be delivered in multiple lot date codes with deliveries separated by two weeks. If applicable, each production lot will be kitted with homogeneous material which is then allocated across multiple lot date code builds to satisfy the deliverable order quantity. When ordered, Group C Inspection, lot qualifications, and/or DPA will be performed on the first build lot within the production lot unless otherwise stated on the purchase order.

3.2. Mechanical

3.2.1. Package Outline

See [Figure 6-8](#).

3.2.2. Thermal Characteristics

The worst-case thermal characteristics are found in [Table 6-3](#).

3.2.3. Lead Forming

When the lead forming option is specified, the applicable leak test specified in screening will be performed after forming.

3.3. Electrical

3.3.1. Input Power

Devices are available with an input voltage of either +5.0 Vdc ($\pm 5\%$) or +3.3 Vdc ($\pm 5\%$). Current is measured, no load, at maximum rated operating voltage.

3.3.2. Temperature Range

Operating range is $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$.

3.3.3. Absolute Pull Range

Absolute pull range is defined as the minimum guaranteed amount the VCXO can be varied about the center frequency (f_0). It accounts for degradations including temperature stability ($-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$), aging (15 years), radiation effects, power supply variations ($\pm 5\%$) and load variations ($\pm 10\%$).

3.3.4. Frequency Aging

When tested in accordance with MIL-PRF-55310 Group B inspection, the 15-year aging projection shall not cause the minimum APR limit to be exceeded.

3.3.5. Operating Characteristics

Symmetrical square wave limits are dependent on the device frequency and are in accordance with [Table 6-1](#). Waveform measurement points and logic limits are in accordance with MIL-PRF-55310. Start-up time is 10.0 ms maximum.

3.3.6. Output Load

ACMOS (10 k Ω , 15 pF) test loads are in accordance with MIL-PRF-55310.

4. Quality Assurance Provisions and Verification

4.1. Verification and Test

Device lots shall be tested prior to delivery in accordance with the applicable Screening Option letter as stated by the 15th character of the part number. [Table 6-4](#) tests are conducted in the order shown and annotated on the appropriate process travelers and data sheets of the governing test procedure. For devices that require Screening Options that include MIL-PRF-55310 Group A testing, the Post-Burn-In Electrical Test and the Group A Electrical Test are combined into one operation.

4.1.1. Screening Options

The Screening Options, by letter, are summarized as:

Table 4-1. Screening Options

Screening Option	Description
A	Modified MIL-PRF-38534 Class K Screening
B	Modified MIL-PRF-55310 Class B Screening & Group A QCI
C	Modified MIL-PRF-55310 (Rev E) Class S Screening & Group A QCI
D	Modified MIL-PRF-38534 Class K Screening & 30-day Aging
E	Modified MIL-PRF-55310 Class B Screening & Groups A & B QCI
F	Modified MIL-PRF-55310 (Rev E) Class S Screening & Groups A & B QCI
G	Modified MIL-PRF-55310 Class B Screening & Post BI Nominal Electricals
S	MIL-PRF-55310 (Rev F) Class S Screening & Groups A & B QCI
X	Engineering Model (EM)

4.2. Optional Design, Test and Data Parameters

The following is a list of design, assembly, inspection, and test options that can be selected or added by purchase order request.

- a. Design Pedigree (choose one as the 5th character in the part number)

Table 4-2. Design Pedigree

Design Pedigree	Description
E	Enhanced Element Evaluation (MIL-PRF-38534 Rev L for Class K components as specified in DOC208191), 100 krad die, Premium Q Swept Quartz
R	Hi-Rel design with 100 krad Class K die, Premium Q Swept Quartz
V	Hi-Rel design with 100 krad Class K die, Non-Swept Quartz
X	Hi-Rel design with Non-Swept Quartz, Class K die
B	Hi-Rel design with Premium Q Swept Quartz, Class B die
C	Hi-Rel design with Non-Swept Quartz, Class B die
D	Hi-Rel design with Non-Swept Quartz and commercial grade components

- b. Input Voltage as the 14th character. See [Ordering Part Number](#).

- c. Not Used

- d. Radiographic Inspection

- e. Group C Inspection: In accordance with (IAW) MIL-PRF-55310, Rev E (required eight destruct specimens)

- f. Group C Inspection: IAW MIL-PRF-55310, Rev E (required eight destruct specimens, includes Random Vibration, MIL-STD-883, Method 1014 Leak Test and Life Test)

- g. Group C Inspection: IAW MIL-PRF-38534, Table C-Xc, Condition PI (requires eight destruct specimens – 5 pc. Life, 3 pc. RGA). Subgroup 1 fine leak test to be performed per MIL-STD-202, Method 112, Condition C.

- h. Internal Water-Vapor Content (RGA) samples and test performance

- i. MTBF Reliability Calculations: IAW MIL-HDBK-217 unless otherwise specified

- j. Worst Case Circuit Analysis: IAW MIL-HDBK-1547 unless otherwise specified

- k. Derating and Thermal Analysis: IAW MIL-HDBK-1547 with $T_j \text{ Max} = +105^\circ\text{C}$; Derated Maximum Operating Temp = $T_j \text{ Max} - \Delta T_j$ unless otherwise specified

- l. Process Identification Documentation (PID)

- m. Customer Source Inspection (pre-crystal mount pre-cap, post-crystal mount pre-cap and final). Due to components being mounted underneath the crystal blank, pre-crystal mount pre-cap inspection should be considered

- n. Destruct Physical Analysis (DPA): IAW MIL-STD-1580 with exceptions as specified in Microchip DOC203982. The DPA leak test specified will agree with the screening option selected.

- o. Qualification: IAW MIL-PRF-55310, Rev F, Table IV (requires 16 destruct specimens). Includes Group III, SG1 through SG6 only. ESD (SG7) not performed

- p. Qualification: IAW EEE-INST-002, Section C4, Table 3, Level 1 or 2 (requires 11 destruct specimens)

- q. High Resolution Digital Pre-Cap Photographs (20 Megapixels minimum)

- r. Hot solder dip of leads with Sn63/Pb37 solder prior to shipping

- s. As Designed Parts, Materials and Processes List

4.2.1. NASA EEE-INST-002

A combination of Design Pedigree R, Option S Screening, and performance of Qualification per EEE-INST-002, Section C4, Table 3 on 11 destruct specimens, meet the requirements of Level 1 and Level 2 device reliability.

4.3. Test Conditions

Unless otherwise stated herein, inspections are performed in accordance with those specified in MIL-PRF-55310. Process travelers identify the applicable methods, conditions, and procedures to be used. Examples of electrical test procedures that correspond to MIL-PRF-55310 requirements are shown in [Table 6-2](#).

4.4. Delta Limit Exception

When MIL-PRF-55310, Revision F was being reviewed for release by manufacturers and users, Microchip and other organizations recommended that burn-in delta limits not be applied to logic-level measurements due to the inconsistency in attempting to measure small changes in logic levels which inherently have ringing in the signal. This is especially true in higher frequency oscillators measured in automated test systems that are affected by cable length that is not representative of the user's application and contact resistance in test fixtures that do not provide a consistent Vcc or Ground connection. The exact test setup conditions may vary slightly from pre-burn-in to post-burn-in and cause small artificial deltas in logic-level measurements that are not indicative of an issue. Any significant changes in logic levels will be reflected in supply current deltas and/or logic levels that exceed the min/max limits. As a result, we take exception to MIL-PRF-55310, Revision F, Para. 4.4.5 and the delta limit for Output Low Level as specified in 4.4.5(c) shall not be applied to Burn-in PDA.

4.5. Deliverable Data

The manufacturer supplies the following data, as a minimum, with each lot of devices:

- a. As applicable to the Screening Option chosen, completed assembly and screening lot travelers, screening data, including radiographic images, and rework history.
- b. Electrical test variables data, identified by unique serial number.
- c. Special items when required by purchase order such as Group C, DPA, and RGA data. Unless otherwise specified on purchase order, all destruct specimens will be shipped. As delivered, all destruct specimens will be identified by subgroup (if applicable) and packaged separately from flight units.
- d. For Design Pedigrees E, R, V, and X, traceability, component LAT, enclosure LAT, and wafer lot specific RLAT data for non-SMD active devices (if applicable).
- e. Certificate of Conformance.

4.6. Discrepant Material

All MRB authority resides with the procuring activity.

4.7. Failure Analysis

Any failure during Qualification or Group C Inspection will be evaluated for root cause. The customer will be notified after occurrence and upon completion of the evaluation.

5. Preparation for Delivery

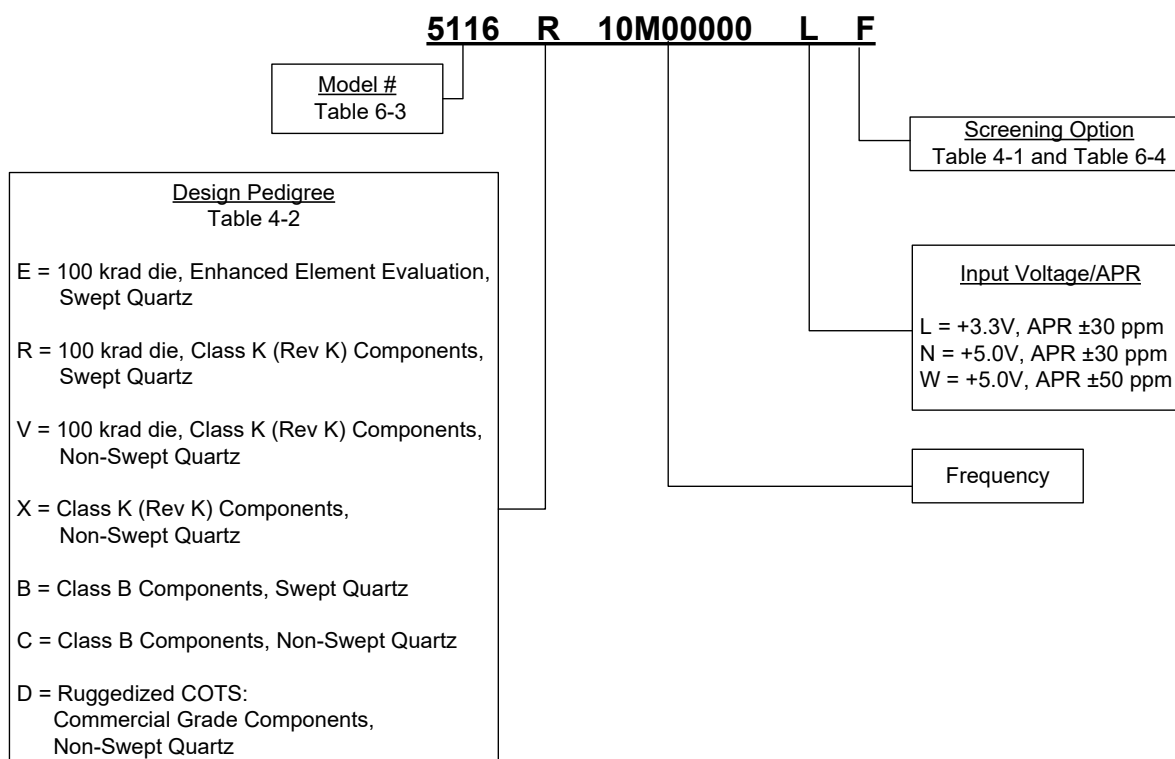
5.1. Packaging

Devices will be packaged in a manner that prevents handling and transit damage during shipping. Devices will be handled in accordance with ANSI/ESD S20.20. Devices will be packaged for transport in accordance with DOC220429. Please note that “one unit per package” is available for a fee; however, this service must be requested as part of the official RFQ.

6. Ordering Information

6.1. Ordering Part Number

The ordering part number consists of an alphanumeric string of 15 continuous characters, without spaces.



6.1.1. Model Number

The device model number is the four (4) digit number 5116.

6.1.2. Design Pedigree

Class S designs correspond to either letter "E", "R", "V" or "X" and Class B designs correspond to either letter "B" or "C". Ruggedized COTS, using commercial grade components, corresponds to letter "D".

6.1.3. Output Frequency

The nominal output frequency is expressed in the format as specified in MIL-PRF-55310 utilizing eight (8) total characters. (Example: 1 MHz = 1M000000, 10 MHz = 10M00000, 100 MHz = 100M0000).

6.1.4. Input Voltage (APR)

"L" for +3.3V (± 30 ppm), "N" for +5.0V (± 30 ppm) and "W" for +5.0V (± 50 ppm) as the 14th character.

6.1.5. Screening Options

The 15th character is the Screening Option selected from [Table 6-4](#).

6.2. Electrical Characteristics and Test Parameters

Optional test and documentation requirements shall be specified by separate purchase order line items (as listed in [4.2. Optional Design, Test and Data Parameters](#)).

Table 6-1. Electrical Performance Characteristics

Label	Value
Frequency Range	1.0 MHz to 100.0 MHz
Temperature Range	-40 °C to +85 °C
Power Supply (Vcc)	+3.3 Vdc $\pm$ 5% or +5.0 Vdc $\pm$ 5%
Absolute Pull Range	$\pm$ 30 ppm or $\pm$ 50 ppm (+/-30 ppm only for +3.3 Vdc)
Control Voltage (Vc) Range	0.3V to +3.0V with Vcc = +3.3V
Control Voltage (Vc) Range	0.5V to +4.5V with Vcc = +5.0V
Slope	Positive
Linearity	10% max.
F vs. V Gain	45 ppm/V min. to 105 ppm/V max.
Start-up Time	10.0 ms max.

Frequency Range (MHz)	Current (mA) (max no load)		Rise / Fall Times ¹ (ns max)	Duty Cycle ¹ (%)
	+5.25V	+3.465V		
1 – 15	15	8	10	45 to 55
>15 – 40	20	15	5	40 to 60
>40 – 60	35	20	5	40 to 60
>60 – 85	45	25	3	40 to 60
>85 – 100	55	35	3	40 to 60
Note:				
1. Waveform measurement points and logic limits are in accordance with MIL-PRF-55310, Para 3.6.20.3.				

Table 6-2. Electrical Test Parameters

Operation Listing	Requirements and Conditions
PERFORMED DURING ALL ELECTRICAL TESTS	
Input Current (no load)	MIL-PRF-55310, Para 4.8.5.1
Initial Accuracy at Reference Temperature	MIL-PRF-55310, Para 4.8.6
Output Logic Voltage Levels	MIL-PRF-55310, Para 4.8.21.3
Rise and Fall Times	MIL-PRF-55310, Para 4.8.22
Duty Cycle	MIL-PRF-55310, Para 4.8.23
Frequency Deviation	MIL-PRF-55310, Para 4.8.31.1
Linearity	MIL-PRF-55310, Para 4.8.31.5 Nominal conditions only
PERFORMED DURING POST BURN-IN ELECTRICAL ONLY	
Overvoltage Survivability	MIL-PRF-55310, Para 4.8.4
Initial Frequency – Temperature Accuracy	MIL-PRF-55310, Para 4.8.10.1
Frequency – Voltage Tolerance	MIL-PRF-55310, Para 4.8.14
Start-up Time	MIL-PRF-55310, Para 4.8.29

Table 6-3. Typical Thermal Characteristics and Weight

Model #	Thermal Resistance Junction to Case θ_{jc} ($^{\circ}\text{C}/\text{W}$)	Δ Junction Temperature T_j ($^{\circ}\text{C}$ @ maximum I_{cc})	Weight (grams)
5116	31.62	9.13	1.2

Note:

1. The maximum power from Table 6-1 is used to calculate the worst case Δ Junction Temperature.

Figure 6-1. Typical Phase Noise Performance at 16 MHz, 3.3V

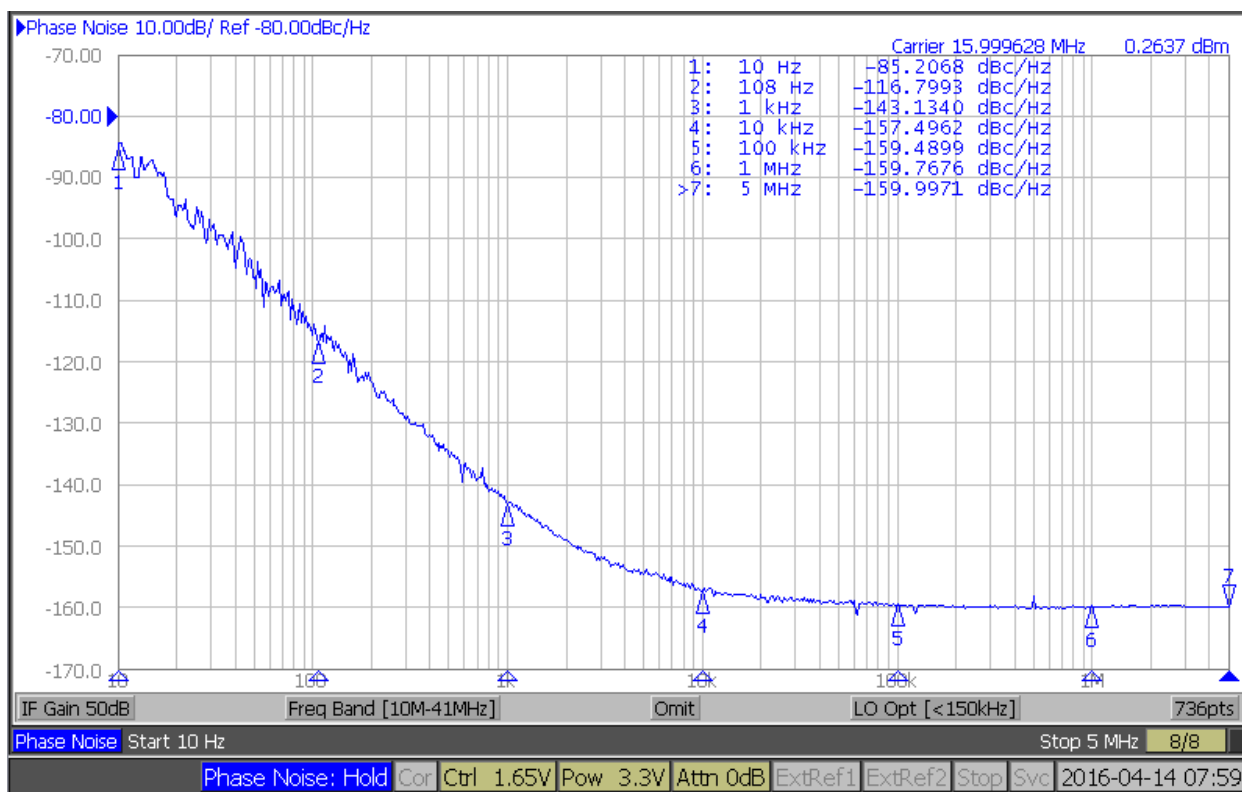


Figure 6-2. Typical Phase Noise Performance at 16 MHz, 5.0V

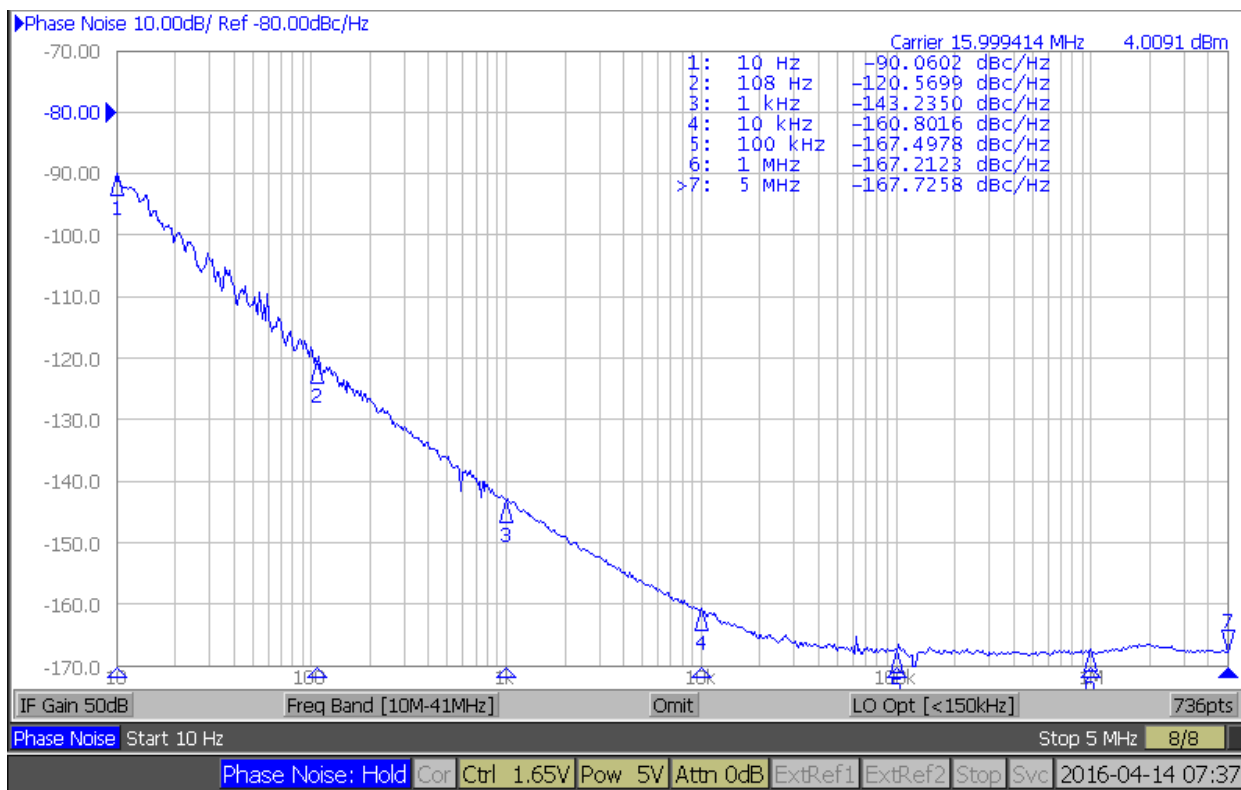


Figure 6-3. Typical Phase Noise Performance at 50 MHz, 3.3V

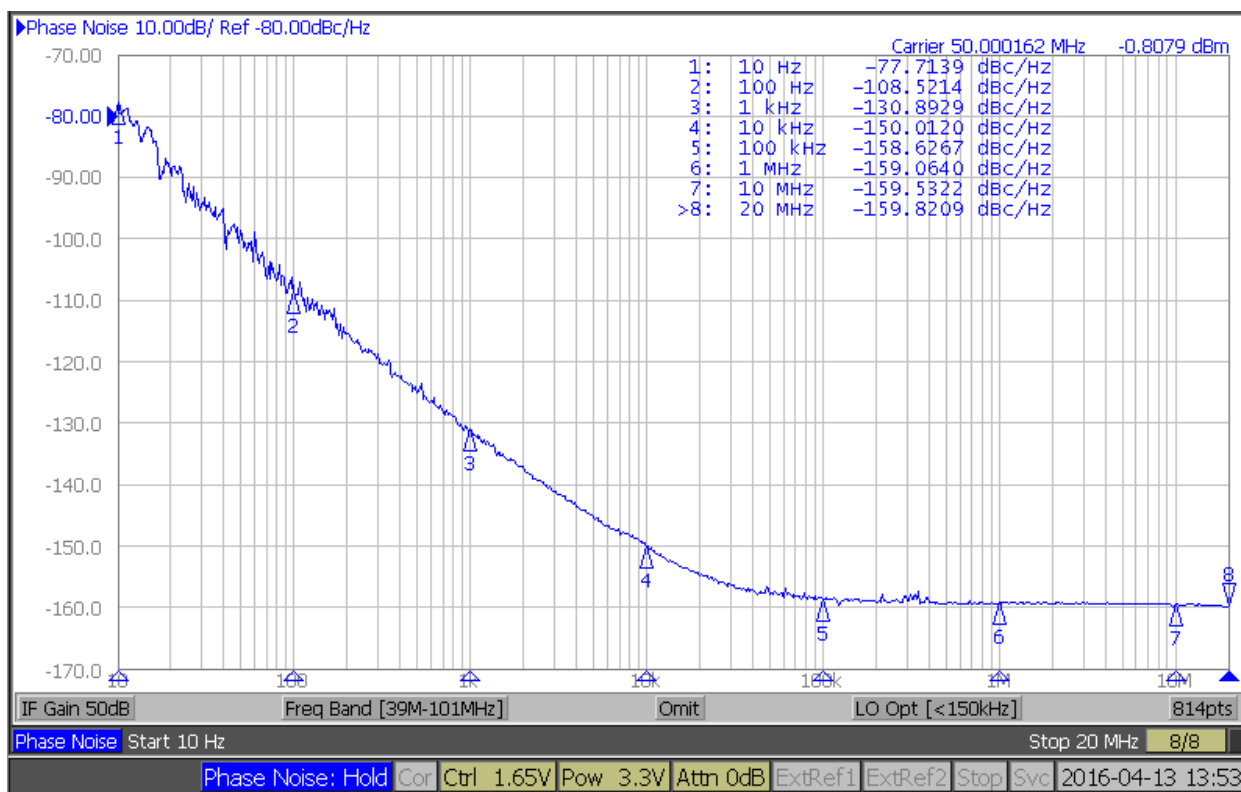


Figure 6-4. Typical Phase Noise Performance at 66 MHz, 3.3V

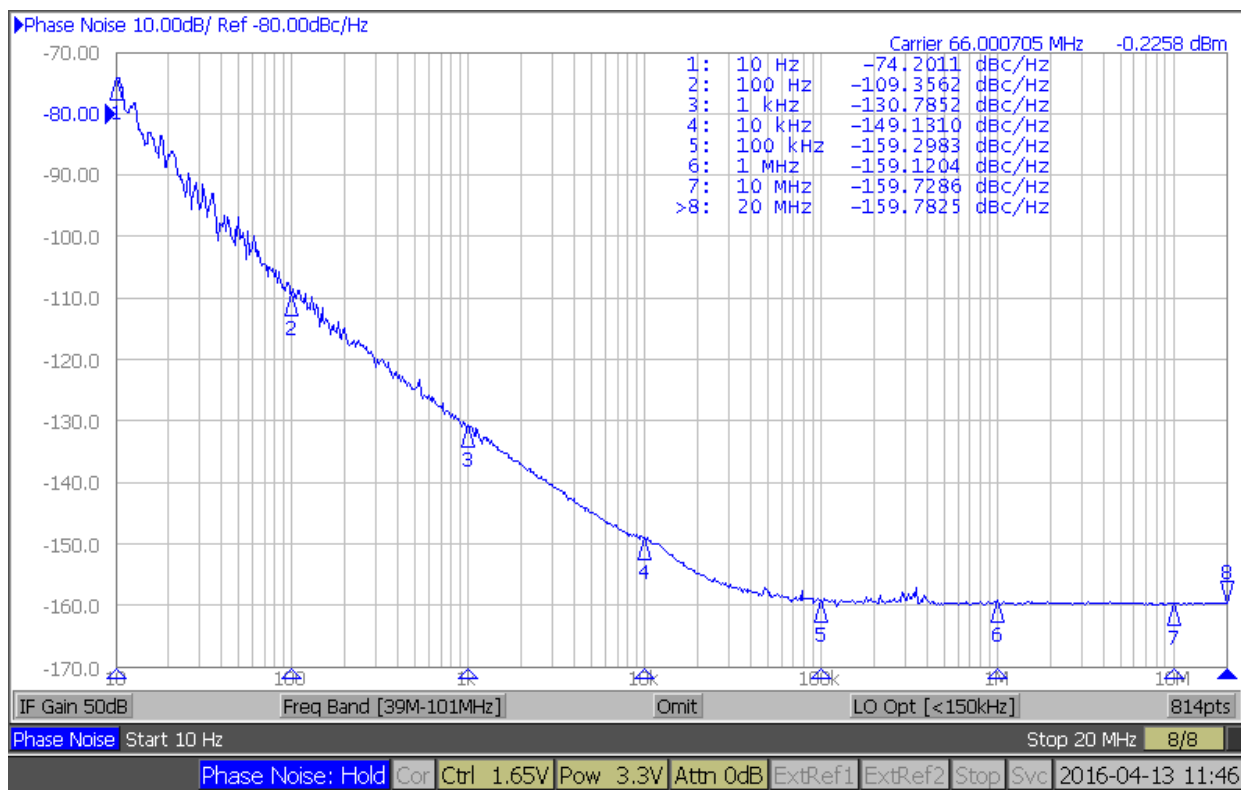


Figure 6-5. Typical Phase Noise Performance at 80 MHz, 3.3V

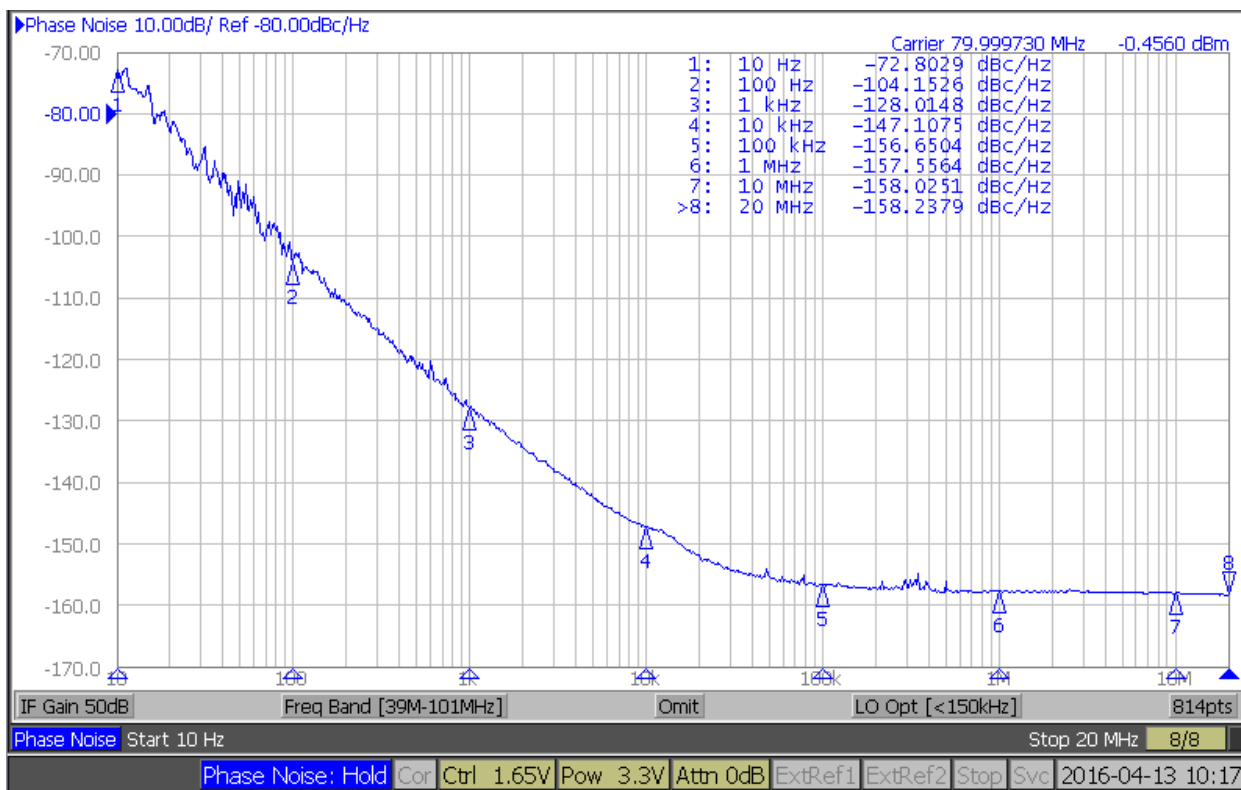


Figure 6-6. Typical Phase Noise Performance at 100 MHz, 3.3V

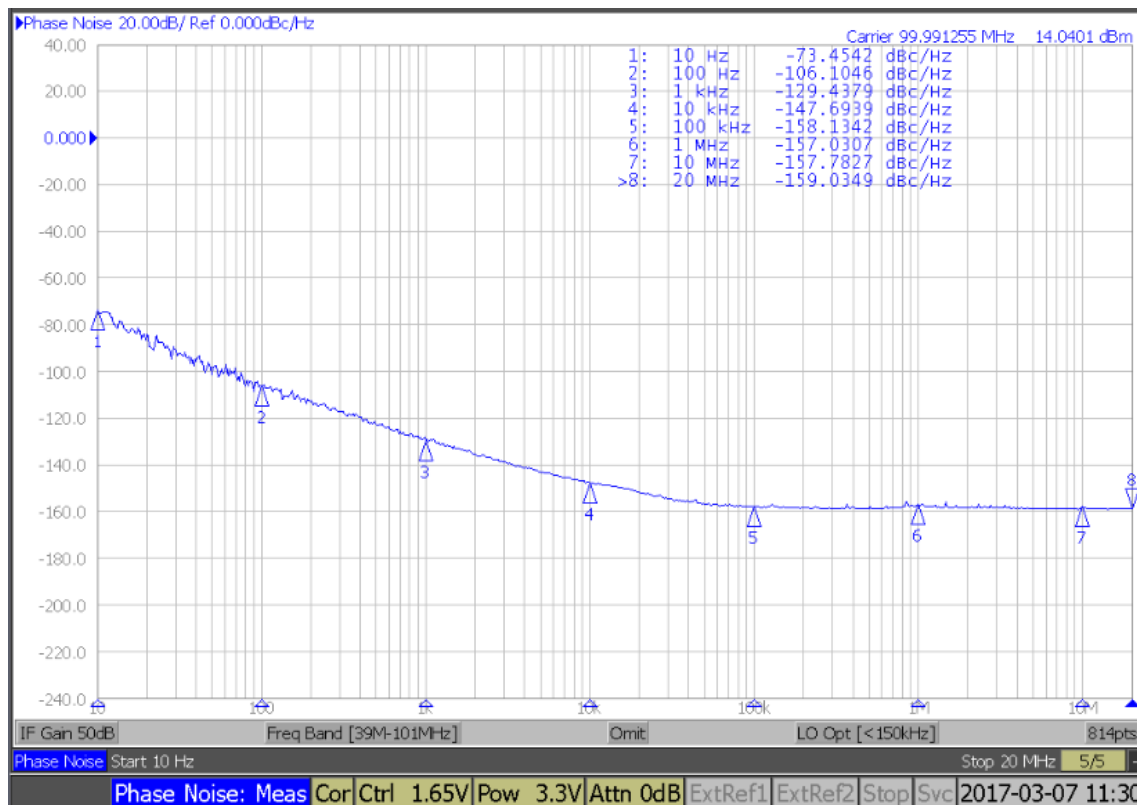


Figure 6-7. Typical Phase Noise Performance at 100 MHz, 5.0V

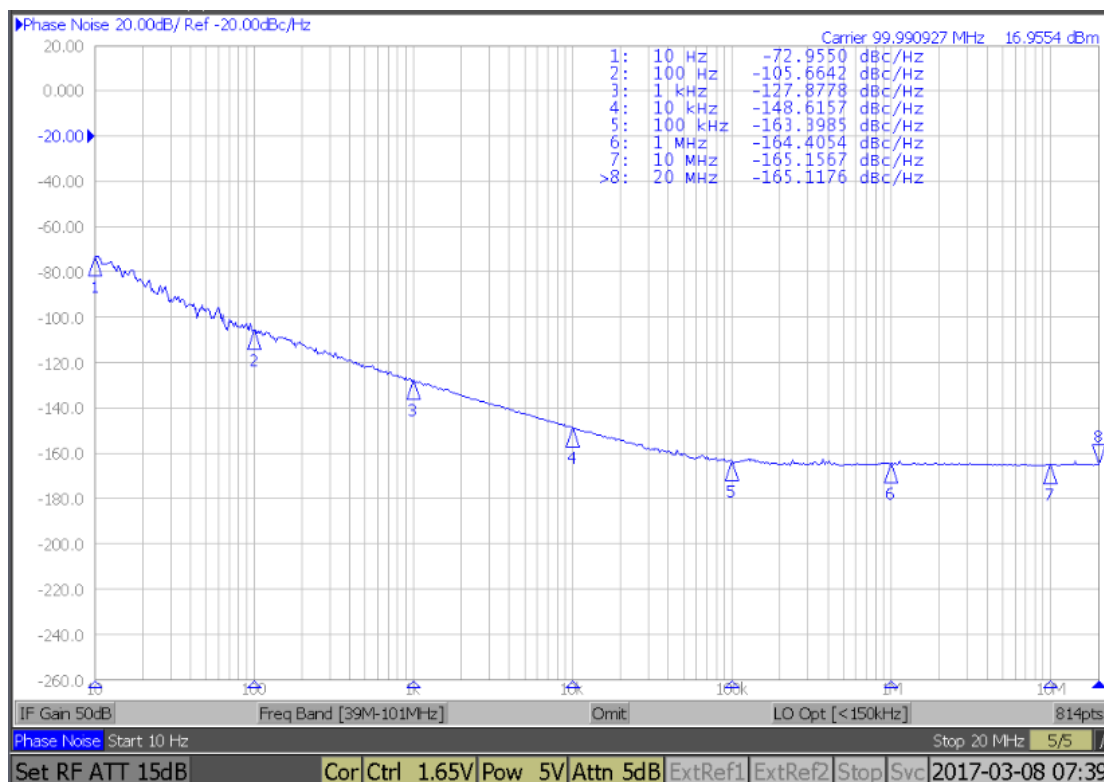


Table 6-4. Screening Test Matrix

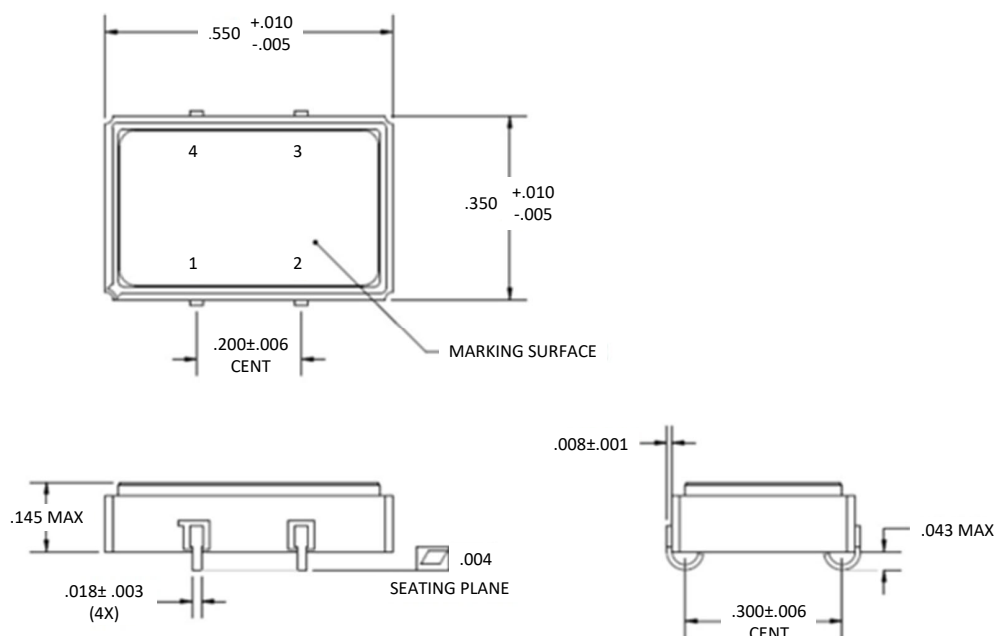
OPN. NO.	Operation Listing	Requirements and Conditions	Option A	Option B	Option C	Option D	Option E	Option F	Option G	Option S	Option X
	SCREENING	MIL Class Similarity (MIL-PRF-55310, Class S/B or MIL-PRF-38534, Class K)	K 100%	B- 100%	S- 100%	K+ 100%	B 100%	S (Rev E) 100%	— 100%	S (Rev F) 100%	EM 100%
1	Non-Destruct Bond Pull	MIL-STD-883, Method 2023	X	NR	X	X	NR	X	NR	X	NR
2	Internal Visual	MIL-STD-883, Method 2017 Class K, Method 2032 Class K	X	X	X	X	X	X	X	X	X
3	Stabilization (Vacuum) Bake	MIL-STD-883, Method 1008, Cond. C, 150°C	X 48 hrs.	X 24 hrs.	X 48 hrs.	X 48 hrs.	X 24 hrs.	X 48 hrs.	X 24 hrs.	X 48 hrs.	X 24 hrs.
4	Random Vibration	MIL-STD-883, Method 2026, Cond. I-B, 15 mins in each axis	NR	NR	NR	NR	NR	NR	NR	X	NR
5	Thermal Shock	MIL-STD-883, Method 1011, Cond. A	NR	NR	X	NR	NR	X	NR	X	NR
6	Temperature Cycle	MIL-STD-883, Method 1010, Cond. B (except Option S), 10 cycles min.	X	X	X	X	X	X	X	X Cond. C	NR
7	Constant Acceleration	MIL-STD-883, Method 2001, Cond. A, Y1 plane only, 5000g	X	X	X	X	X	X	X	X	NR
8	Particle Impact Noise Detection	MIL-STD-883, Method 2020, Cond. B (except Option S)	X	X	X	X	X	X	NR	X Cond. A	X ⁵
9	Electrical Testing, Pre Burn-In	Perform tests in Table 6-3 . Nominal Vcc, nominal temperature	X	X	X	X	X	X	X	X	X
10	1 st Burn-In	MIL-STD-883, Method 1015, Cond. B	X 160 hrs.	X 160 hrs.	X 240 hrs.	X 160 hrs.	X 160 hrs.	X 240 hrs.	X 160 hrs.	X 240 hrs.	NR
11	Electrical Testing, Intermediate	Perform tests in Table 6-3 . Nominal Vcc, nominal temperature	X	NR	NR	X	NR	NR	NR	NR	NR
12	2 nd Burn-In	MIL-STD-883, Method 1015, Cond. B	X 160 hrs.	NR	NR	X 160 hrs.	NR	NR	NR	NR	NR
13	Electrical Testing, Post Burn-In (Group A) ⁴	Perform tests in Table 6-3 . Nominal Vcc and extremes, nominal temperature and extremes	X	X	X	X	X	X	X nom. Vcc	X	NR
14	Seal: Fine Leak	MIL-STD-202, Method 112, Cond. C (5 x 10 ⁻⁸ atm cc/sec max)	X	X	X	X	X	X	X	NR	X
	Seal: Gross Leak	MIL-STD-202, Method 112, Cond. D									
15	Seal: Fine Leak	MIL-STD-883, Method 1014, Cond. A2 or B1	NR	NR	NR	NR	NR	NR	NR	X	NR
	Seal: Gross Leak	MIL-STD-883, Method 1014, Cond. B2 or B3									
16	Radiographic Inspection	MIL-STD-883, Method 2012	X	AR	AR	X	AR	X	NR	X	NR
17	Solderability	MIL-STD-883, Method 2003	1	1	1	1	1	1	1	1	NR
18	External Visual and Mechanical	MIL-STD-883, Method 2009	X ²	X ²	X ²	X ²	X ²	X ²	X ²	X ²	X ²
19	Aging, 30 Day ³ (M55310 Group B)	MIL-PRF-55310, para. 4.8.35.1	NR	NR	NR	X	13 pcs.	X	NR	X	NR
20	Group C Inspection (optional)	See 4.2. Optional Design, Test and Data Parameters for details of supplier recommended Group C Inspection options	4.2(g)	4.2(e)	4.2(e)	4.2(g)	4.2(e)	4.2(e)	4.2(e)	4.2(f)	NR

Legend: X = Required, NR = Not Required, AR = As Required

Notes:

1. Performed at package LAT. Include LAT data sheet.
2. When specified, RGA samples will be removed from the lot after completion of this operation. Use of Screening failures require customer concurrence.
3. See [3.3.4. Frequency Aging](#).
4. See [4.4. Delta Limit Exception](#).
5. PIND PDA does not apply.

Figure 6-8. Model 5116 Package Outline



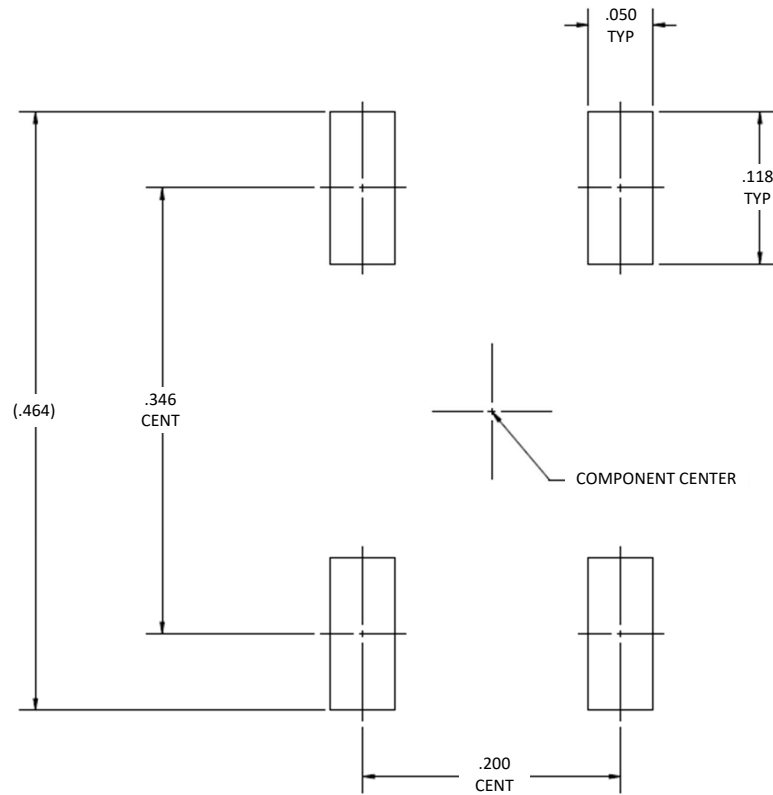
Pin	Function
1	Control Voltage
2	GND/Case
3	Output
4	Vcc

Notes:

- Lid is internally tied to case ground.
- Pin numbers are for reference only and do not appear on the unit.
- Tolerance (unless otherwise specified): XXX± .005 [.130], XX± .01 [.25].

7. Recommended Land Pattern

Figure 7-1. Model 5116



8. Revision History

Revision	Date	Description
B	02/2026	<ul style="list-style-type: none"> Updated Hi-Rel Standard revision to H Added support contact information to General Made minor grammatical changes throughout Updated Section 2.4.3 Assembly to Microchip Updated SEL LET value in Section 3.1.5 Radiation Added sentence to the end of Section 3.1.6 Packages Added Premium Q to row B of Table 4-2 Updated Section 4.2 Optional Design, Test and Data Parameters <ul style="list-style-type: none"> Updated line b and added cross reference Added MIL-HDBK information to line i Added DPA leak test information to line n Added destruct specimens to Section 4.2.1 NASA EEE-INST-002 Moved Section 4.3.1 Delta Limit Exception to be 4.4 Added destruct specimens information to line c of previous Section 4.4 Deliverable Data. Now Section 4.5 Added ANSI/ESD information to Section 5.1 Packaging Added example to Section 6.1.3 Output Frequency Changed named of Section 6.2 to Electrical Characteristics and Test Parameters Incorporated notes into tables Removed fast/slow start from Table 6-2 Electrical Test Parameters Added Note 2 to Table 6-3 Typical Thermal Characteristics and Weight Added Note 5 and updated links in row 20 to Table 6-4 Screening Test Matrix Added notes to the table for Figure 6-8 Model 5116 Package Outline Moved Recommended Land Pattern from the Appendix to Section 7.0
A	03/2025	Converted Vectron Hi-Rel Standard revision G to Microchip branding with document number DS00005895 revision A. Minor text changes throughout.

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